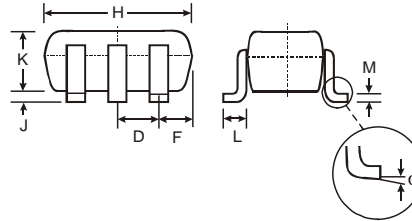
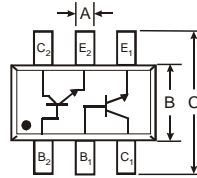


### Features

- Epitaxial Planar Die Construction
- Intrinsically Matched NPN Pair (Note 1)
- Small Surface Mount Package
- 2% Matched Tolerance,  $h_{FE}$ ,  $V_{CE(SAT)}$ ,  $V_{BE(SAT)}$
- **Lead Free/RoHS Compliant (Note 3)**

### Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.015 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
$\alpha$	8°	
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous	$I_C$	200	mA
Power Dissipation (Note 2)	$P_d$	200	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
1. Built with adjacent die from a single wafer.
  2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  3. No purposefully added lead.

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	60	—	V	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	—	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
Base Cutoff Current	I <sub>BL</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
<b>ON CHARACTERISTICS (Note 4)</b>					
DC Current Gain (Note 5)	h <sub>FE</sub>	40 70 100 60 30	— — 300 — —	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 50mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1.0V
Collector-Emitter Saturation Voltage (Note 5)	V <sub>CE(SAT)</sub>	—	0.20 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage (Note 5)	V <sub>BE(SAT)</sub>	0.65 —	0.85 0.95	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage Matching	ΔV <sub>BE</sub>	—	1	mV	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	4.0	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	8.0	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	
Output Admittance	h <sub>oe</sub>	1.0	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	—	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	—	5.0	dB	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 100μA, R <sub>S</sub> = 1.0kΩ, f = 1.0kHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>d</sub>	—	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Rise Time	t <sub>r</sub>	—	35	ns	V <sub>BE(off)</sub> = -0.5V, I <sub>B1</sub> = 1.0mA
Storage Time	t <sub>s</sub>	—	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Fall Time	t <sub>f</sub>	—	50	ns	I <sub>B1</sub> = I <sub>B2</sub> = 1.0mA

- Notes:
- Short duration pulse test used to minimize self-heating effect.
  - The DC current gain, h<sub>FE</sub>, (matched at I<sub>C</sub> = 10mA and V<sub>CE</sub> = 1.0V) Collector Emitter Saturation Voltage, V<sub>CE(SAT)</sub>, and Base Emitter Saturation Voltage, V<sub>BE(SAT)</sub> are matched with typical matched tolerances of 1% and maximum of 2%.

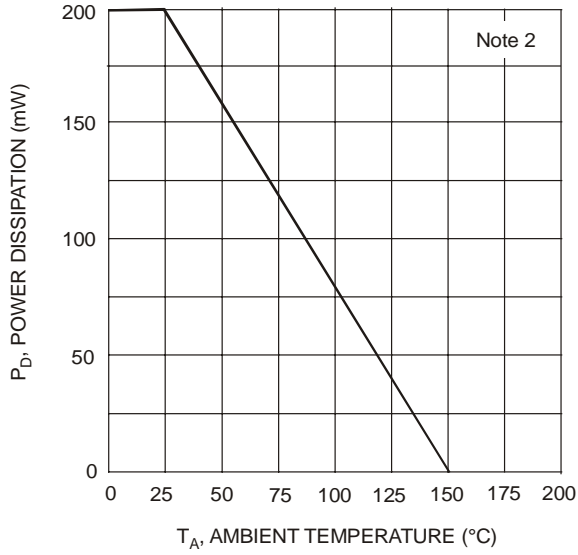


Fig. 1, Max Power Dissipation vs Ambient Temperature

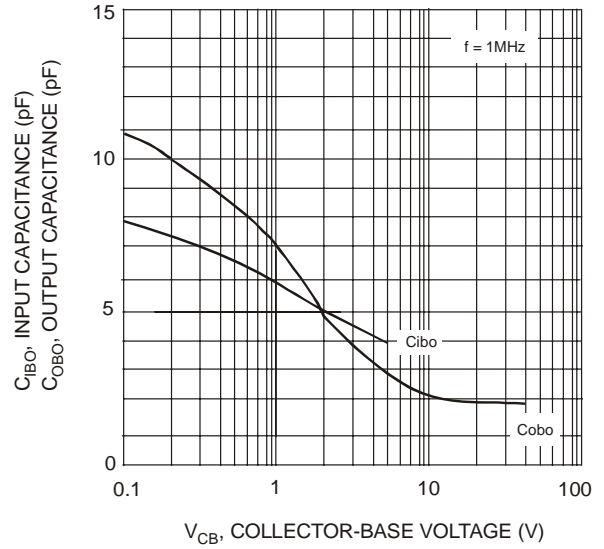


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

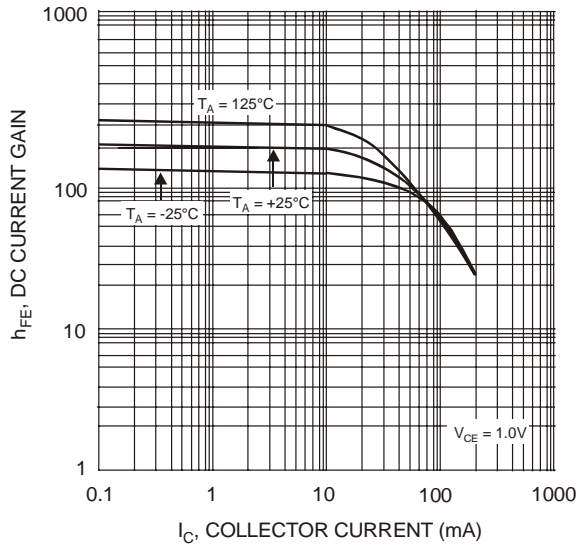


Fig. 3, Typical DC Current Gain vs Collector Current

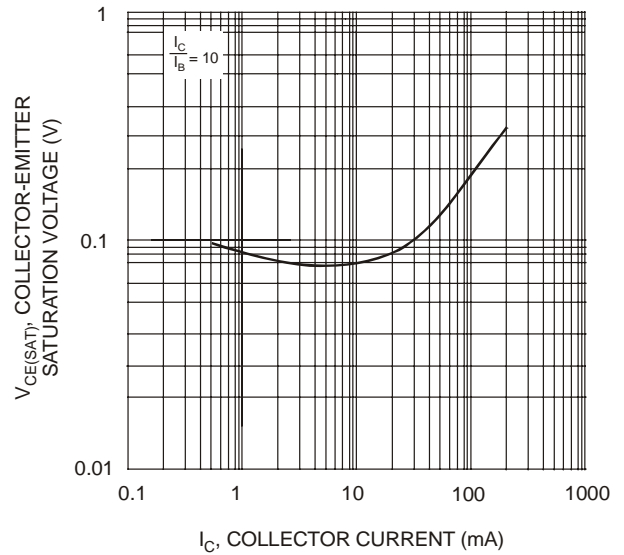


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

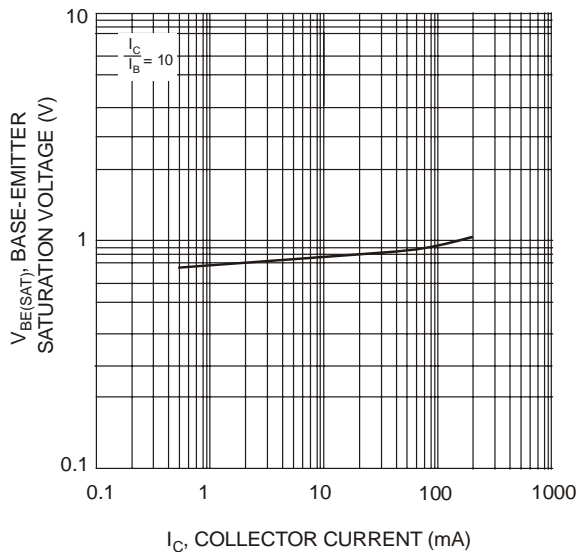


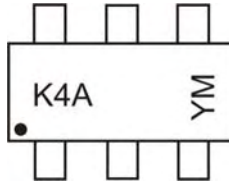
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

**Ordering Information** (Note 6)

Device	Packaging	Shipping
DMMT3904W-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



K4A = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: T = 2006  
 M = Month ex: 9 = September

Data Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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